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Depositor: Karen Cinc-Mars

*Karen Cinc-Mars 8/7/03*  
(Signature & date)

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re application of : August 7, 2003  
Deok-Kee Kim et al. : Group Art Unit:  
Serial No. 10/604,384 : Examiner:  
Filed: 07/16/2003 : International Business Machines Corporation  
2070 Route 52  
Hopewell Junction, NY 12533

**TITLE: SIMPLIFIED TOP OXIDE LATE PROCESS**

**INFORMATION DISCLOSURE STATEMENT**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, Virginia 22313-1450

Sir:

Pursuant to the duty of disclosure set forth in 37 C.F.R. 1.56, and further pursuant to the provisions of 37 C.F.R. 1.97 and 1.98, applicants hereby respectfully submit copies of the prior patents and publications as listed on Form PTO-1449, attached hereto.

In citing these documents, no representation is made nor intended as to the pertinency or non-pertinency of the art, that better art than that listed is not available, or that other art is not applicable.

Respectfully submitted,  
Kim et al.

By

*Steven Capella*  
Steven Capella, Attorney  
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<b>INFORMATION DISCLOSURE CITATION</b> <i>(Use several sheets if necessary)</i>				Docket Number (Optional) <b>FIS920030088US1</b>		Application Number <b>10/604,384</b>	
				Applicant(s) <b>Deok-Kee Kim et al.</b>			
				Filing Date <b>07/16/2003</b>	Group Art Unit		
<b>U.S. PATENT DOCUMENTS</b>							
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<b>FOREIGN PATENT DOCUMENTS</b>							
REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO
<b>OTHER DOCUMENTS</b> <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>							
		A Highly Cost Efficient 8F2 DRAM Cell with a Double Gate Vertical Transistor Device for 100 nm and Beyond, R. Weis et al., Infineon Technologies, IEDM 01-414, pp. 18.7.1-18.7.4, 3/01 IEEE					
<b>EXAMINER</b>				<b>DATE CONSIDERED</b>			
<b>EXAMINER:</b> Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							